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This application is a continuation of copending International Application No. PCT/DE99/02927, filed September 14, 1999, which designated the United States and which was not published in the English language. -

In the Claims:

Claim 7 (amended). A method of producing an integrated circuit configuration, which comprises:

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forming a diffusion barrier layer on a substrate having at least a first insulating layer with a first conductive structure embedded therein;

forming a second insulating layer on the diffusion barrier layer;

forming a contact hole into the second insulating layer above the first conductive structure, wherein the surface of the first conductive structure is covered with the diffusion barrier layer within the hole;

forming spacers on side walls of the contact hole, the spacers acting as a barrier to diffusion of a material from the first conductive structure into the second insulating layer;

opening the contact hole as far as a surface of the first conductive structure; and

A2
(Cont'd)

forming in the contact hole a second conductive structure
conductively connected to the first conductive structure.
